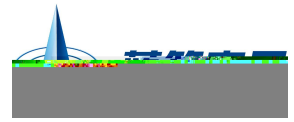
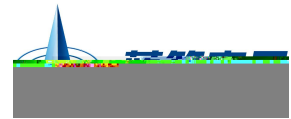


F	2018-7				
G	2019-11-30	2	上限由原来的 改为		
H	2022-7-9	2 3	庞隆基申请 上限由原来的 改为 (典型值 改成), 更新曲线图		

Rev.H Jul.-2022

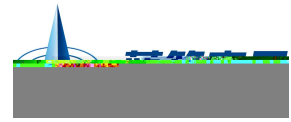


TO-220 P MOS
P-CHANNEL MOSFET in a TO-220 Plastic Package.



Parameter	Symbol	Rating	Unit	
Drain-Source Voltage	V_{DS}	-60	V	
Drain Current	$I_D(T_C=25^\circ C)$	-50	A	
Drain Current - Pulsed	I_{DM}	-200	A	
Gate-Source Voltage	V_{GS}	± 20	V	
Power Dissipation	$P_D(T_C=25^\circ C)$	118	W	
Single Pulsed Avalanche Energy	E_{AS}	250	mJ	
Avalanche Current(L=0.5mH)	I_{AS}	25	A	
Junction and Storage Temperature Range	T_j, T_{stg}	-55 to 150		
Thermal resistance, junction - ambient	$t \leq 10s$	$R_{\theta JA}$	15	°C/W
	Steady-State		60	
Thermal resistance, junction - case	Steady-State	$R_{\theta JC}$	1.1	

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Drain-Source Breakdown Voltage	BV_{DSS}	$V_{GS}=0V$ $I_D=-250\mu A$	-60	-68		V
Zero Gate Voltage Drain Current	I_{DSS}	$V_{DS}=-60V$ $V_{GS}=0V$			-1.0	μA
		$V_{DS}=-48V$ $T_C=150^\circ C$			-10	
Gate-Body Leakage Current Forward	I_{GSS}	$V_{GS}=\pm 20V$ $V_{DS}=0V$			± 0.1	μA
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS}=V_{GS}$ $I_D=-250\mu A$	-1	-1.6	-3	V
Static Drain-Source On-Resistance	$R_{DS(on)}$	$V_{GS}=-10V$ $I_D=-20A$		30	35	m
	$R_{DS(on)}$	$V_{GS}=-4.5V$ $I_D=-10A$		40	45	m
Drain-Source Diode Forward Voltage	V_{SD}	$V_{GS}=0V$ $I_S=-1A$			-1.2	V
Gate resistance	R_g			10		
Input Capacitance	C_{iss}			3200		pF
Output Capacitance	C_{oss}	$V_{DS}=-25V$ $f=1.0MHz$ $V_{GS}=0V$		800		pF



Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Turn-On Delay Time	$t_{d(on)}$	$V_{GS}=-10V$ $V_{DS}=-30V$ $R_L=1.5$ $R_{GEN}=3 \Omega$		12		ns
Turn-On Rise Time	t_r			14.5		
Turn-Off Delay Time	$t_{d(off)}$			38		
Turn-Off Fall Time	t_f			15		

